

THE SPECIFICATION OF AlGaAs IR LED CHIP "NR4B-23"

1. DESCRIPTION

This is a AlGaAs near infrared LED chip. It is N-side up. The peak wavelength is 700 nm (Typ.).

2. ELECTRO - OPTICAL CHARACTERISTICS (Ta=25deg. C)

CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage (V_F) IF=20mA		1.8		V
Reverse Voltage (V_R) IR=10uA	5			V
Radiated Power ¹⁾ (Po) IF=20mA	1.0			mW
Peak Wavelength (λ_p) IF=20mA		700		nm
Spectral Radiation Bandwidth ($\Delta\lambda$) IF=20mA		30		nm

1) LED chip is mounted on TO-18 gold header without resin coated.

3. ABSOLUTE MAXIMUM RATINGS

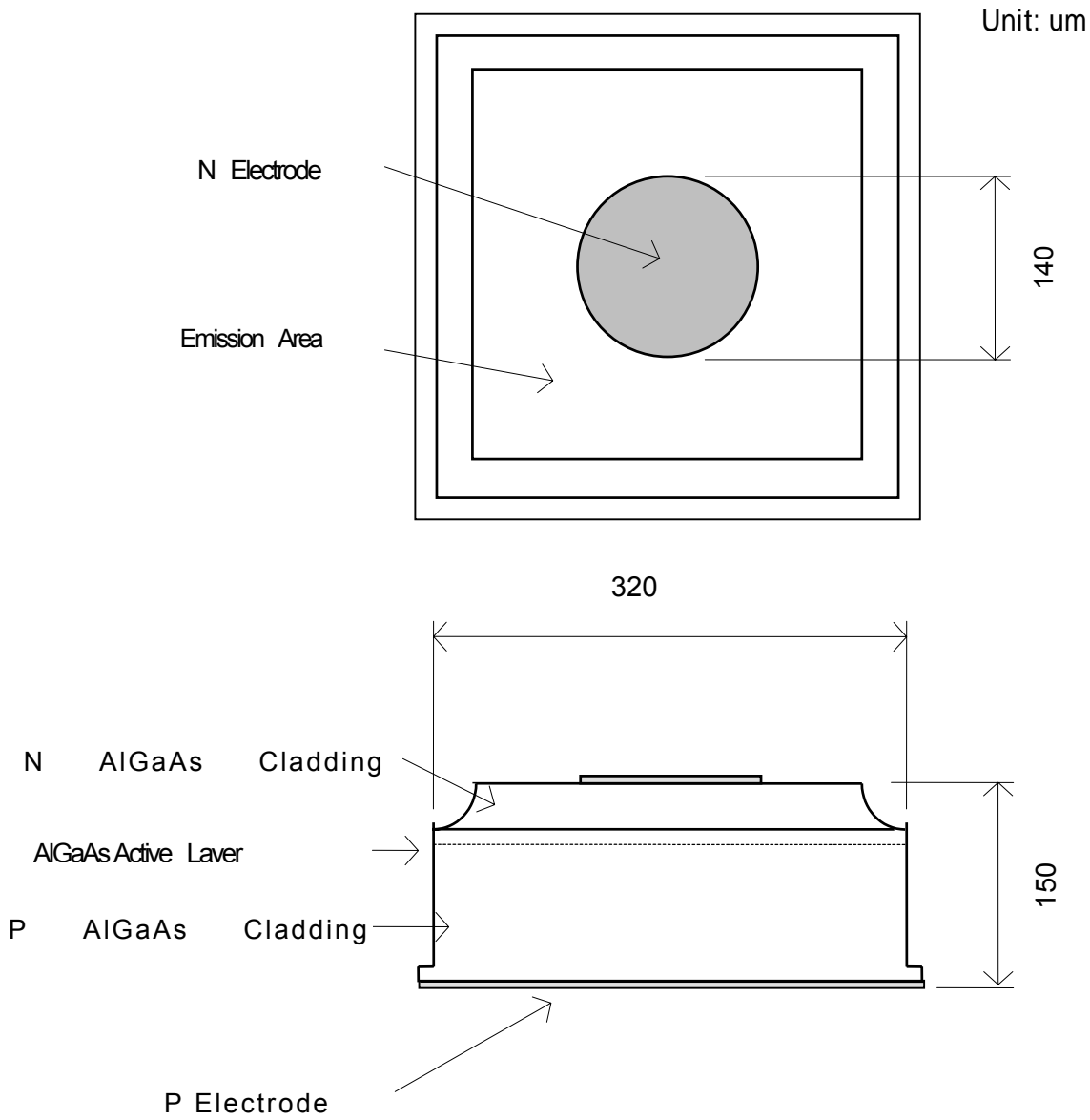
Continuous Maximum Forward Current	: 50 mA(DC)
Reverse Voltage	: 5 V(IR=10uA)
Storage Temperature	
while on mylar membrane	: 0 to 40 deg. C
after removal from mylar membrane	: -40 to 100 deg. C

4. PHYSICAL CHARACTERISTICS AND STRUCTURE

- 1)Material : AlGaAs
- 2)Structure : Double Hetero Structure
- 3)Junction Size : 0.320mmX0.320mm
- 4)Thickness : 0.150mm
- 5)Bond Pad Size : 0.140mm diameter
- 6)Anode Metallization : Gold Alloy
- 7)Cathode Metallization: Gold Alloy

Physical Dimensions

Model NR4B-23



Remark: This specification is for reference purpose only, and subject to change without prior notice.
Approved specification shall be obtained for the regular purchase.